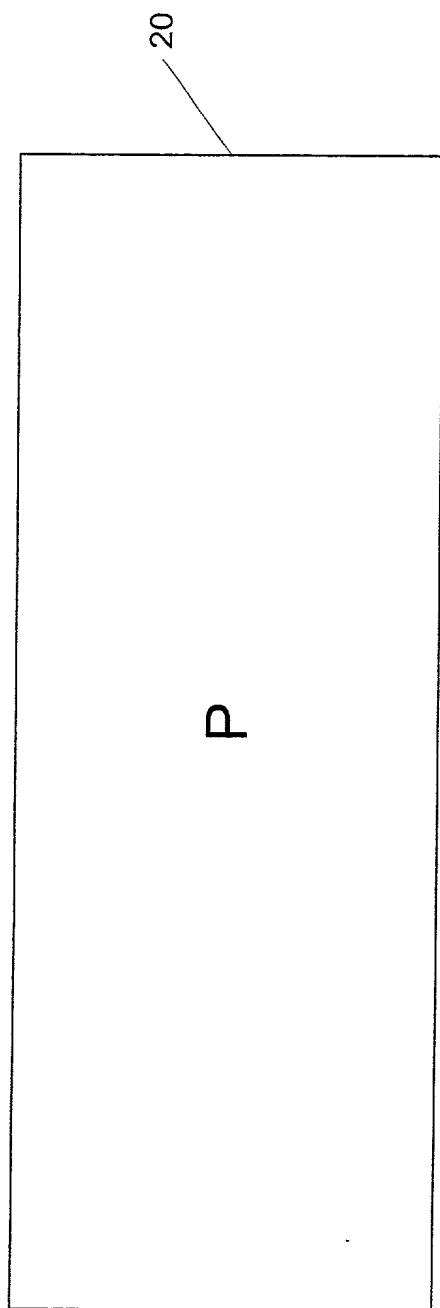


Fig. 1

[illegible]

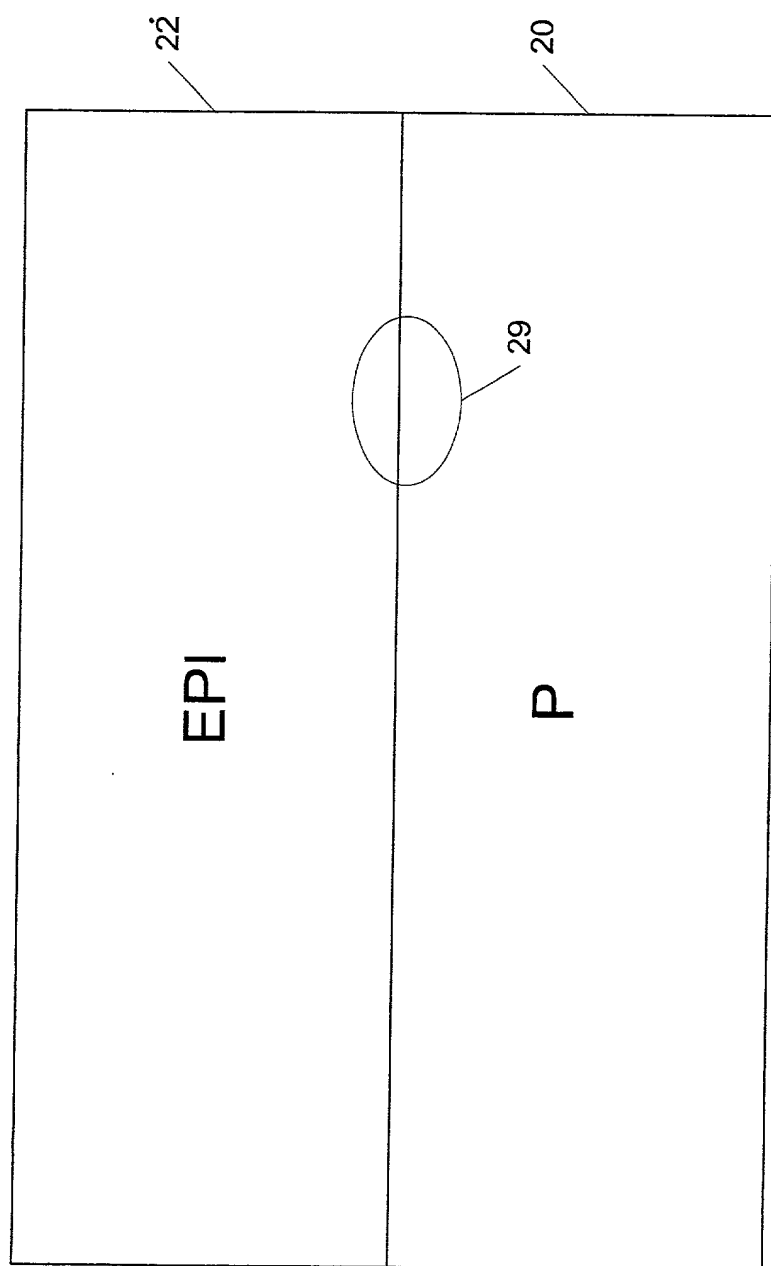


Fig. 2b

FIG. 2c is a cross-sectional view of a semiconductor device, showing a substrate 20, an epitaxial layer 22, and a series of rectangular features 24. A circular feature 29 is also shown within the substrate 20.

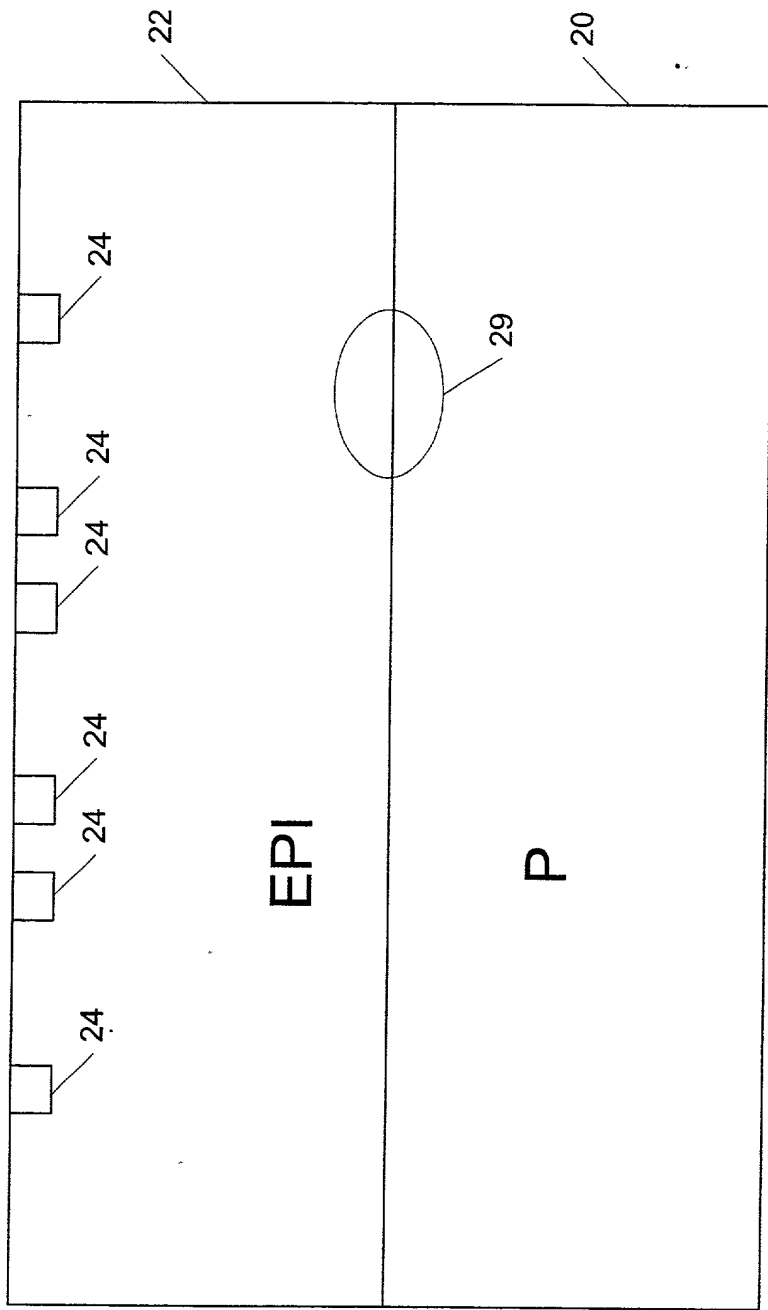


Fig. 2c

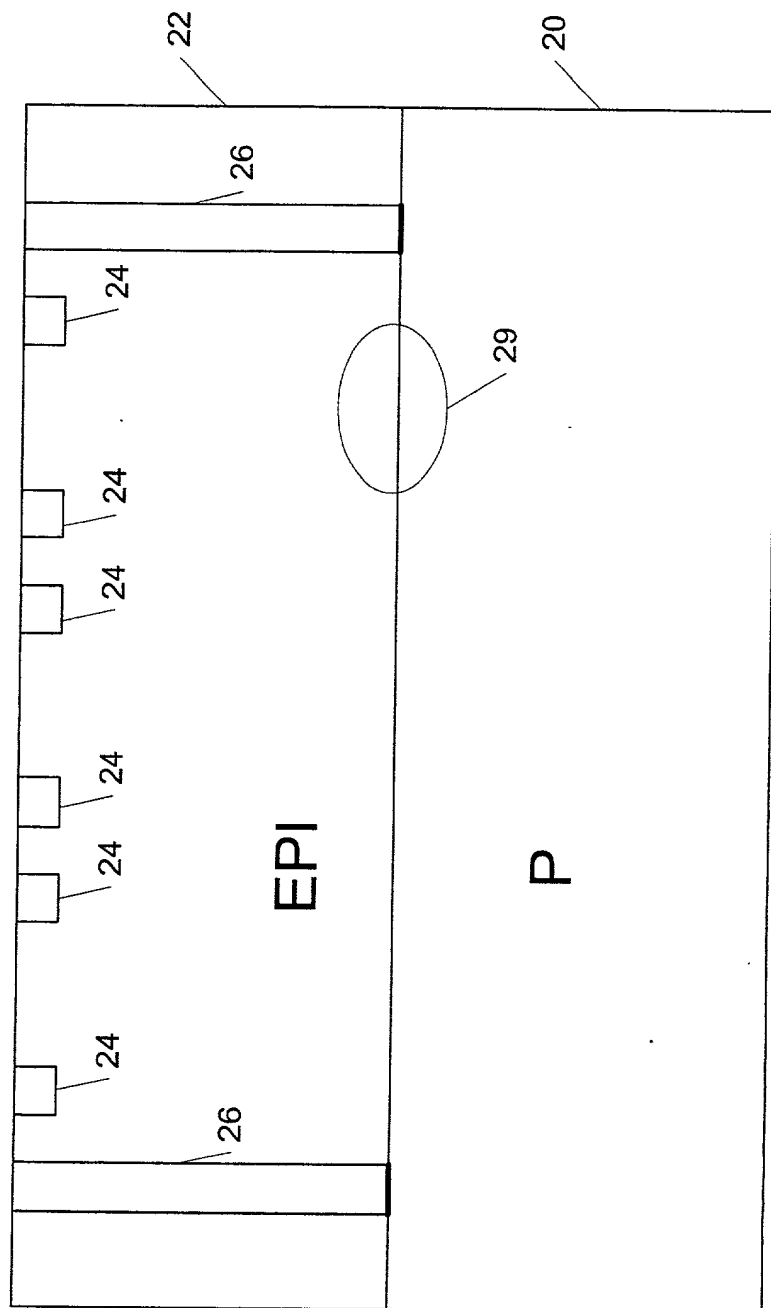


Fig. 2d

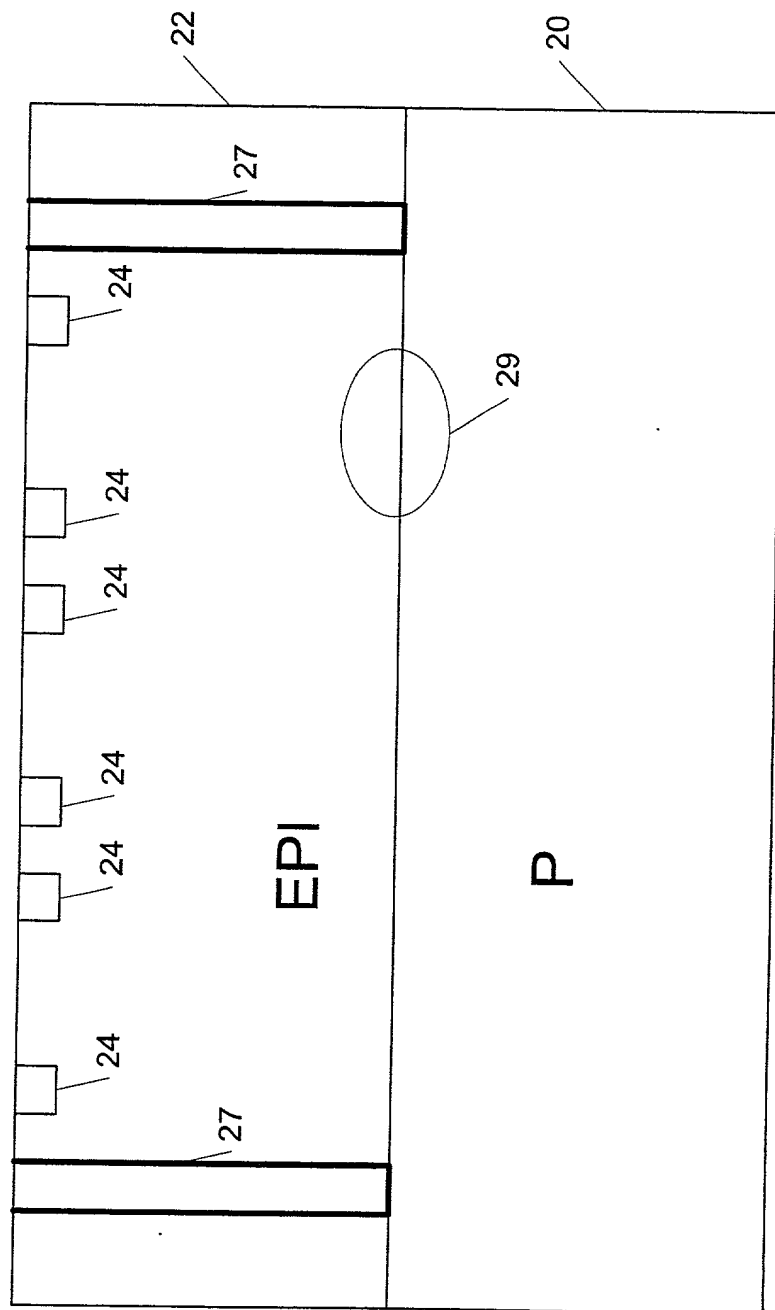


Fig. 2e

Fig. 2f

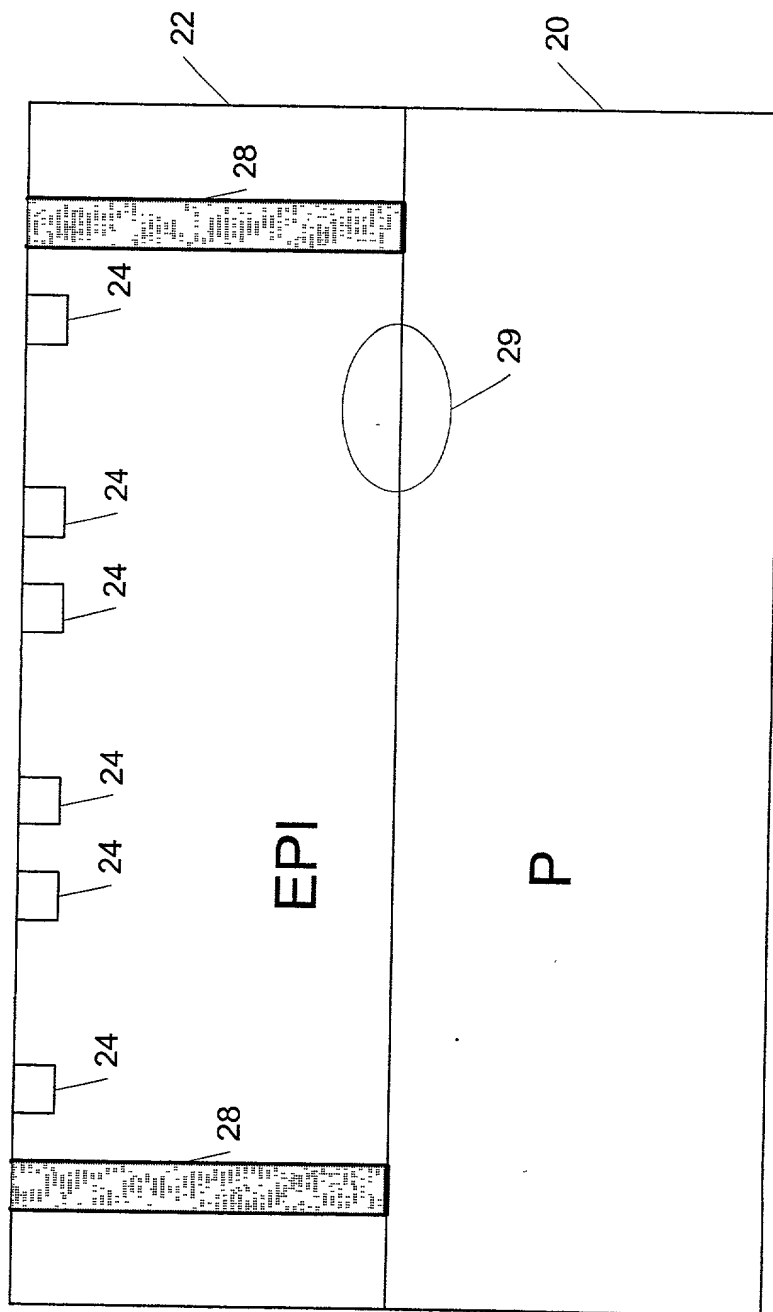


Fig. 2f

FIG. 2g is a schematic diagram of a semiconductor device 20, showing a cross-sectional view of a substrate 22 with a series of gates 24 and a series of source/drain regions 28. The device is formed on a substrate 22, and the gates 24 are formed on the substrate 22. The source/drain regions 28 are formed on the substrate 22, and the gates 24 are formed on the substrate 22. The device is formed on a substrate 22, and the gates 24 are formed on the substrate 22. The source/drain regions 28 are formed on the substrate 22, and the gates 24 are formed on the substrate 22.

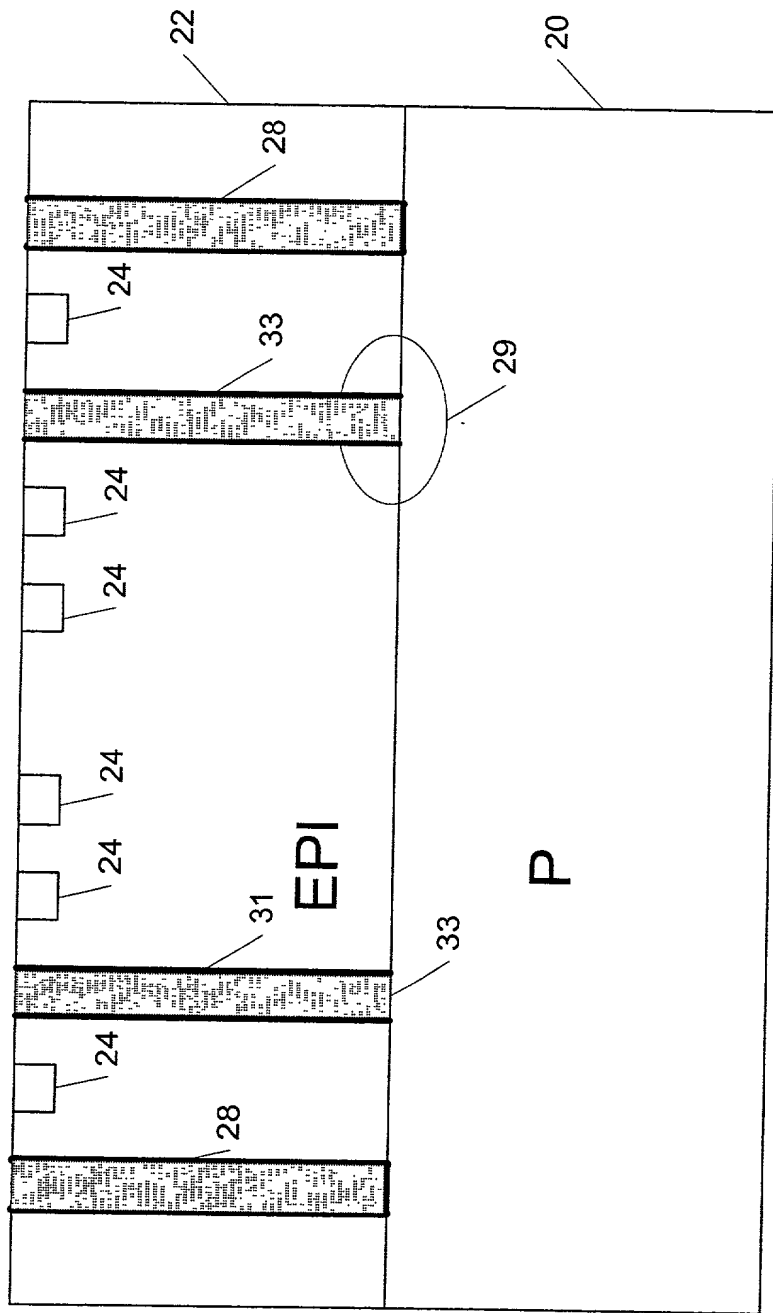


Fig. 2g



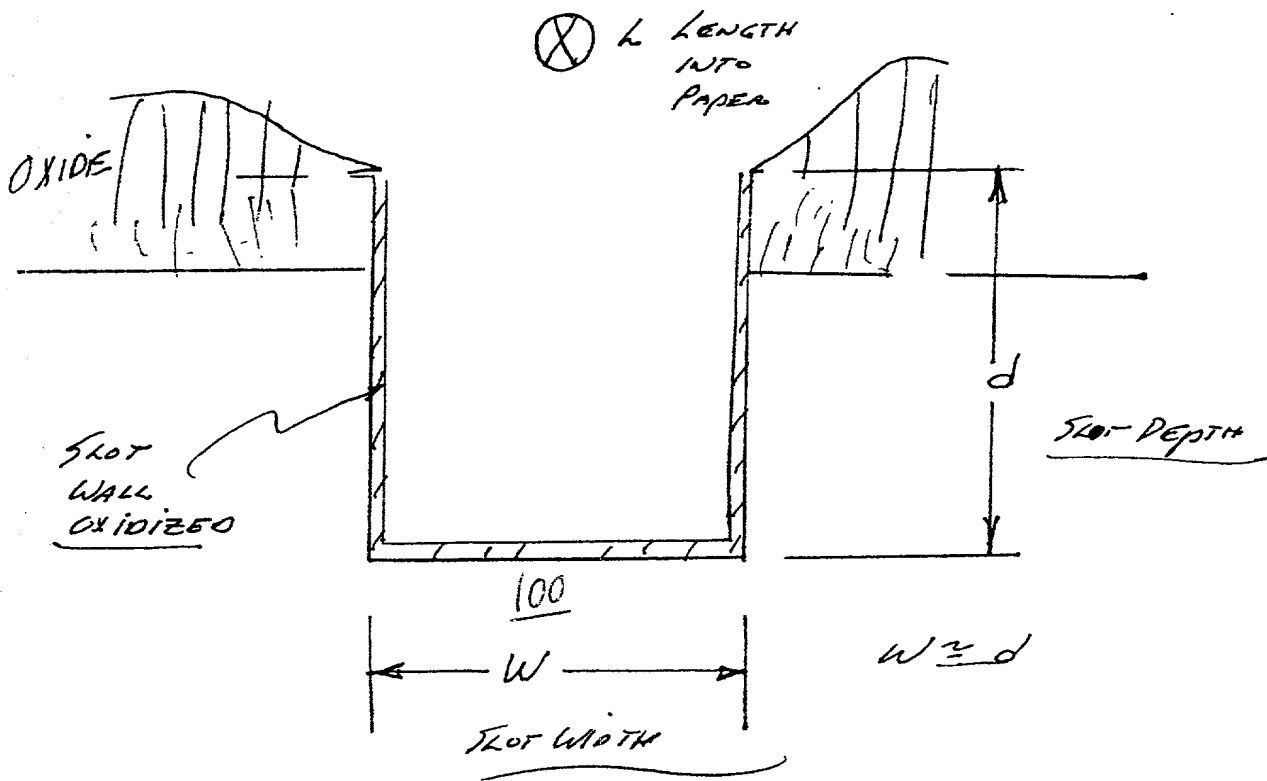


Fig. 3

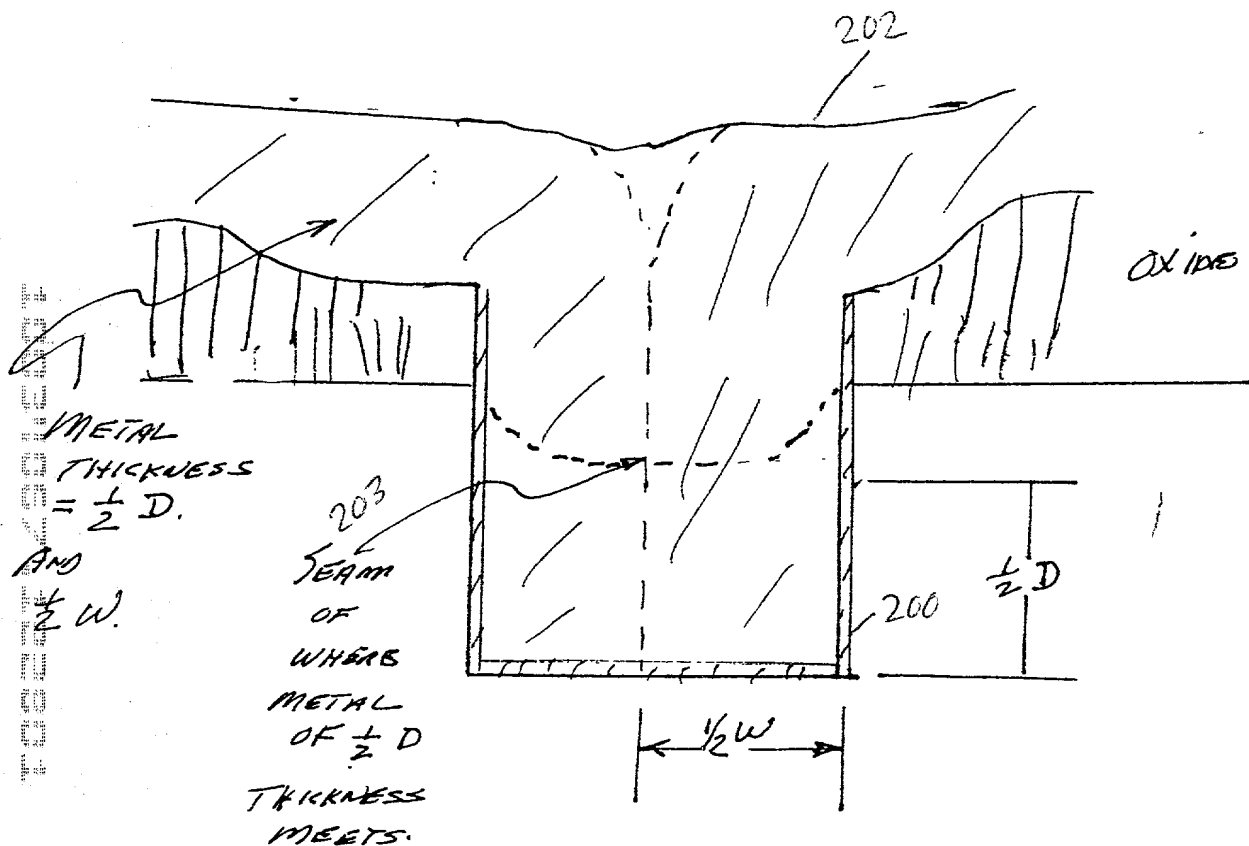
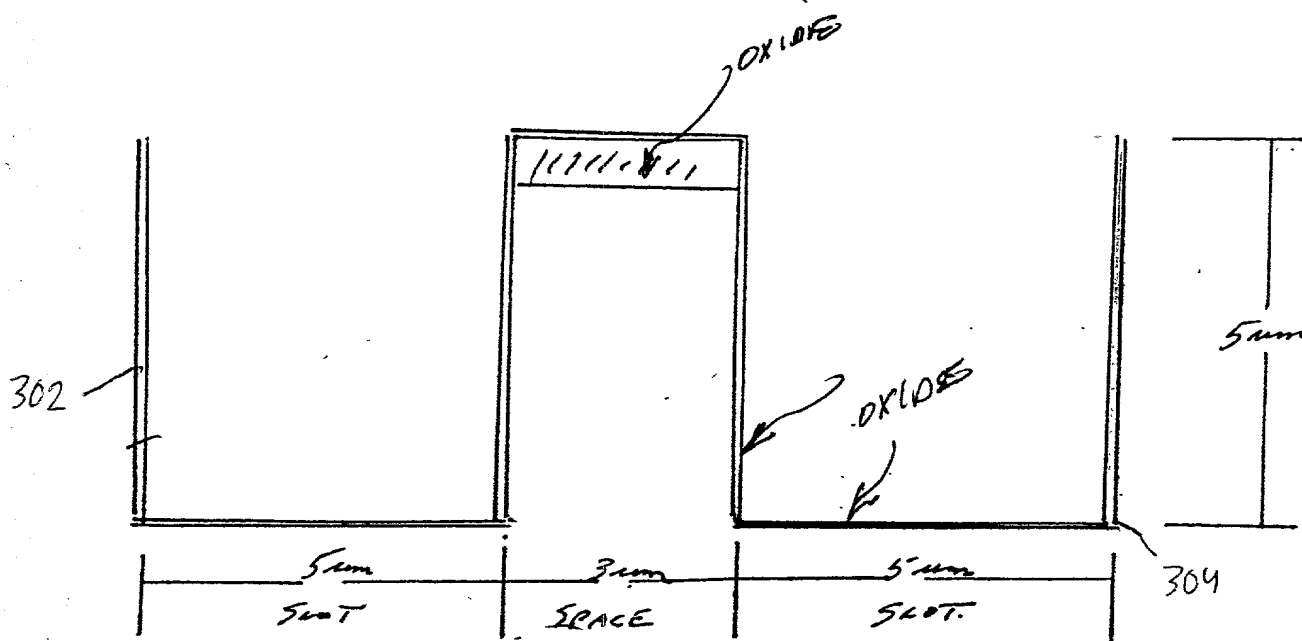
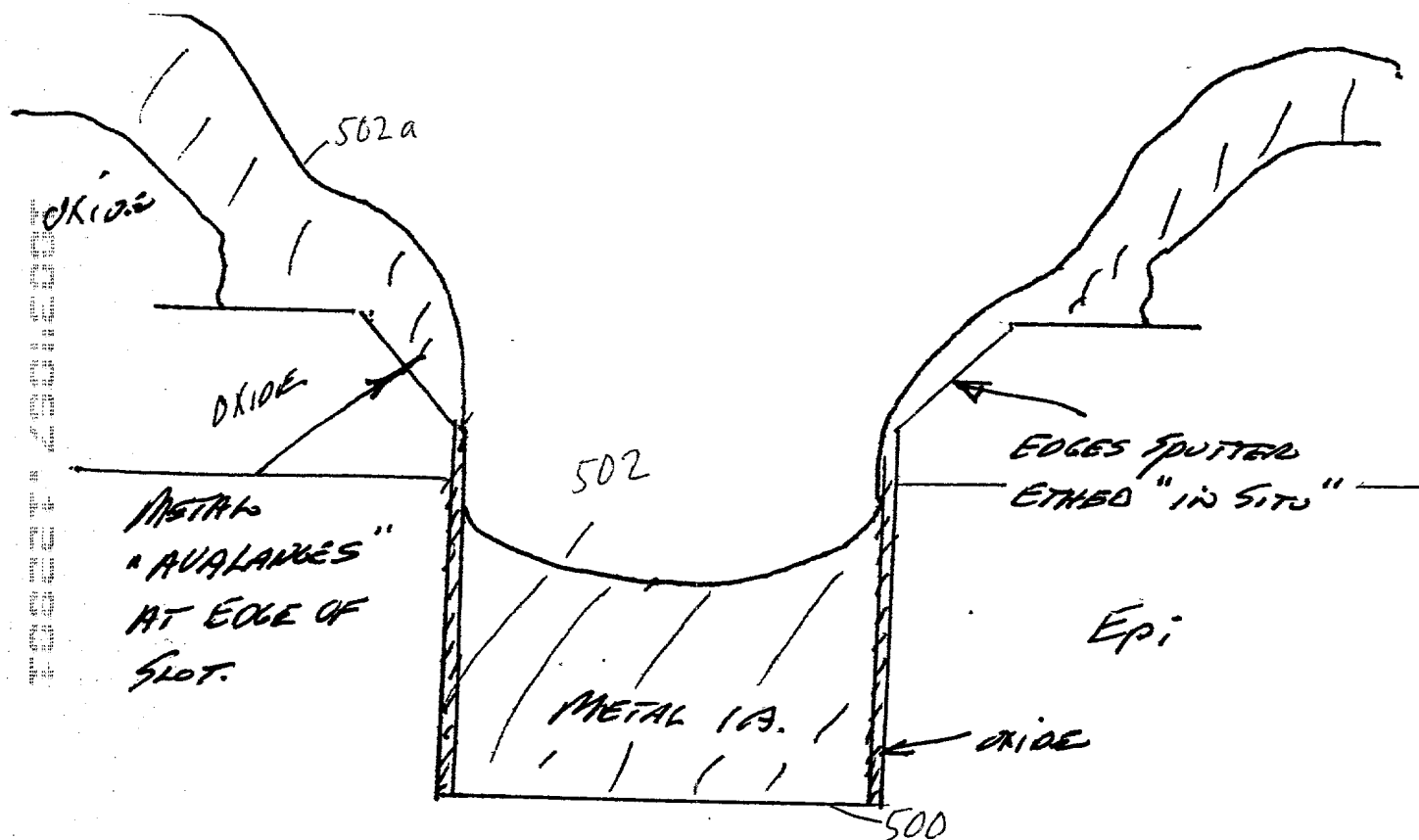


Fig. 4



DOUBLE SLOT FOR  
DOUBLE WIDTH OF METAL.  
3mm SPACE BETWEEN SLOTS

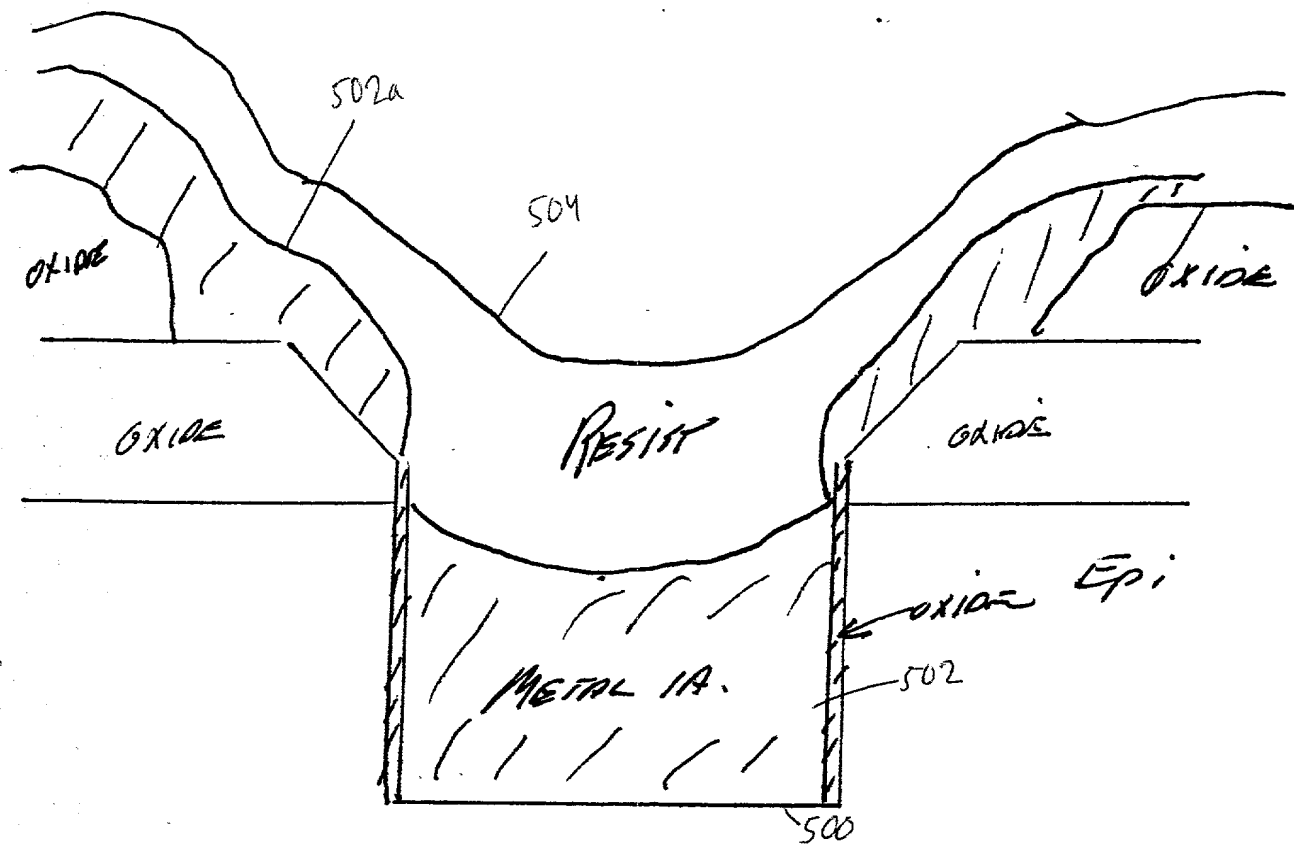
Fig. 4a



Prior TO METAL 1A BEING  
SPUTTERED, THE EDGES OF THE OXIDES  
ARE SPUTTERED ETCHED "IN SITU" &  
1A DEPOSITED

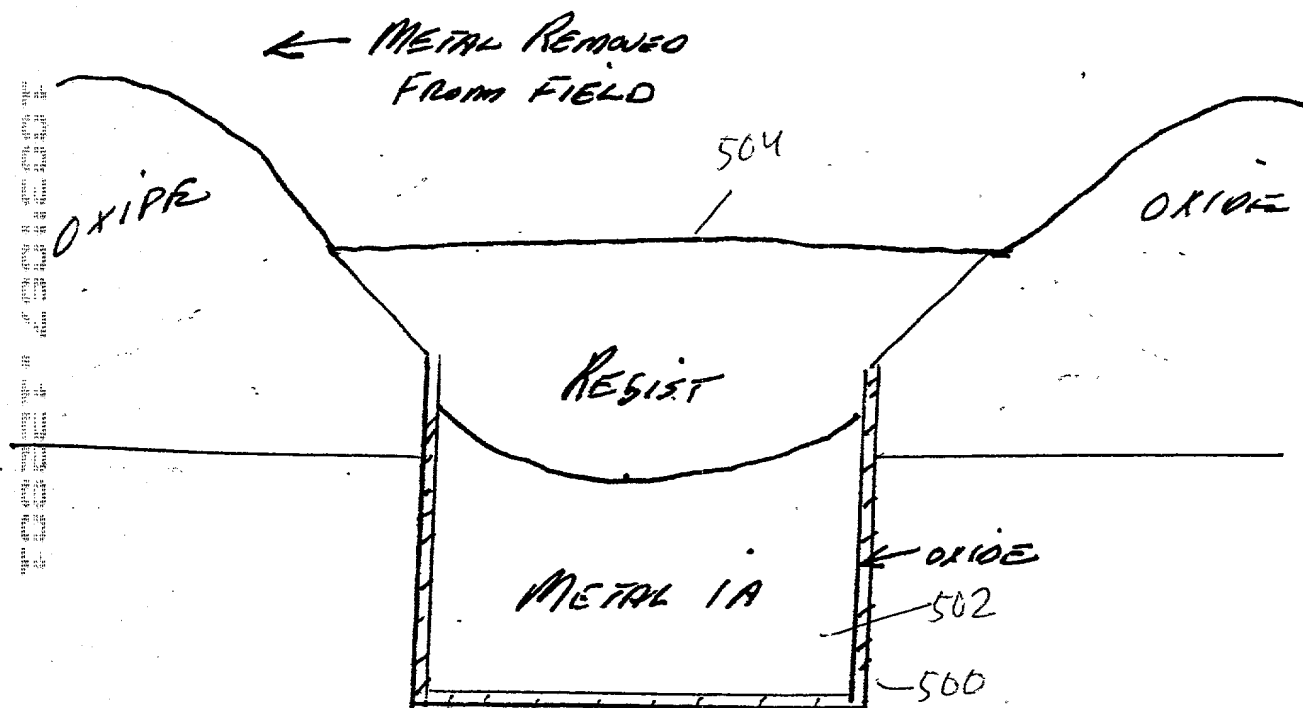
Fig. 5

It is a drawing of a cross-section of a semiconductor device. It shows a substrate with a metal layer (500) and an oxide layer (502). A resist layer (504) is applied over the oxide layer, and it is thicker in the slots (502a). The oxide layer is labeled 'OXIDE' and 'OXIDE Epi'. The metal layer is labeled 'METAL 1A.'. The resist layer is labeled 'RESIST'. The slots are labeled '502a'.



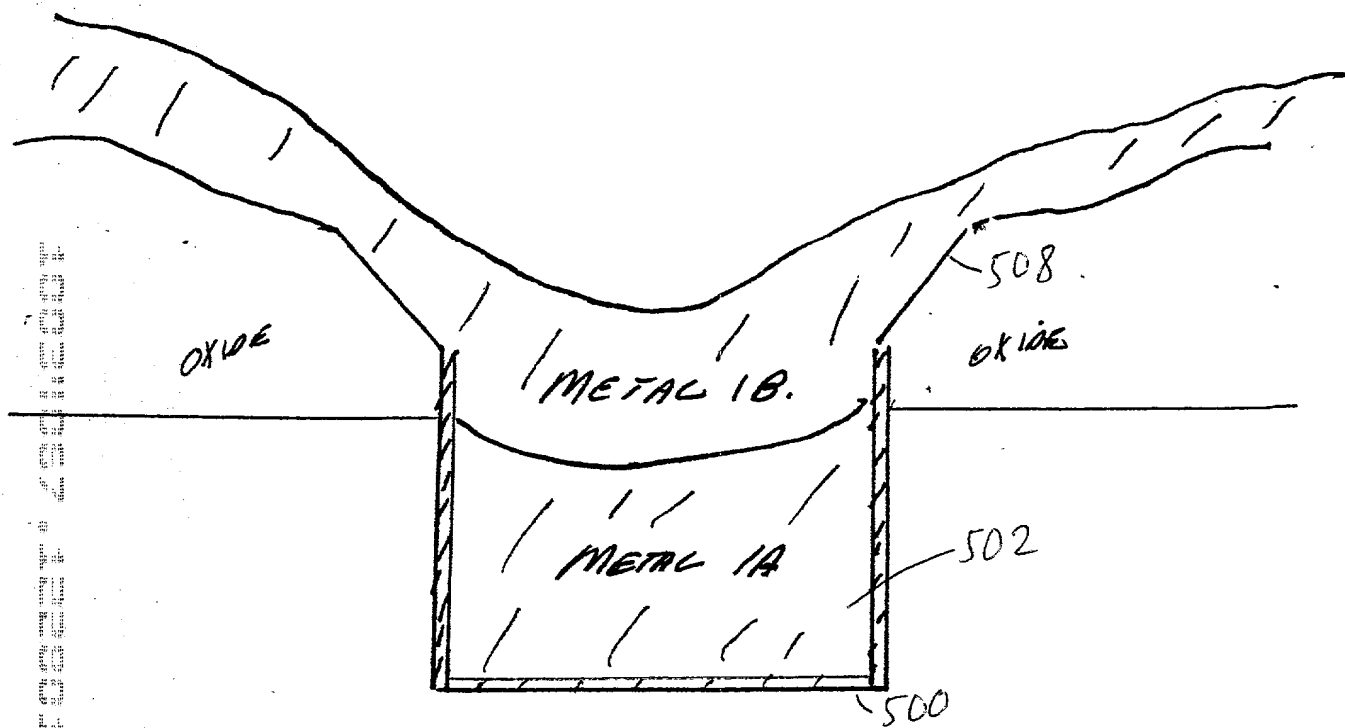
RESIST COATING - THICK IN THE  
SLOTS

Fig. 6



RESIST PLANNED ETCHED.  
 LEAVING RESIST IN FLOTS.  
 FIELD METAL ETCHED OFF.

Fig. 7



RESIST STRIPPED & SECOND  
METAL 1B SPUTTER DEPOSITED

Fig. 8

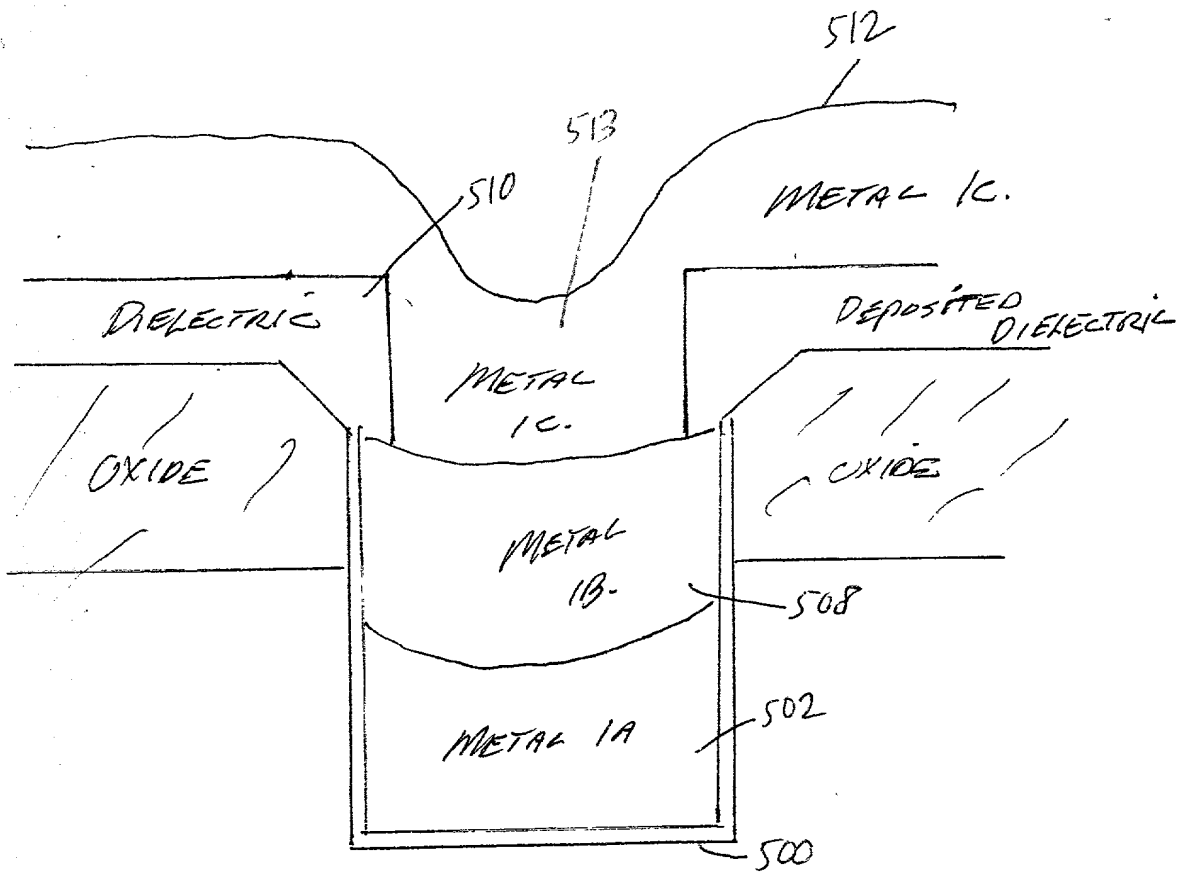


Fig. 9



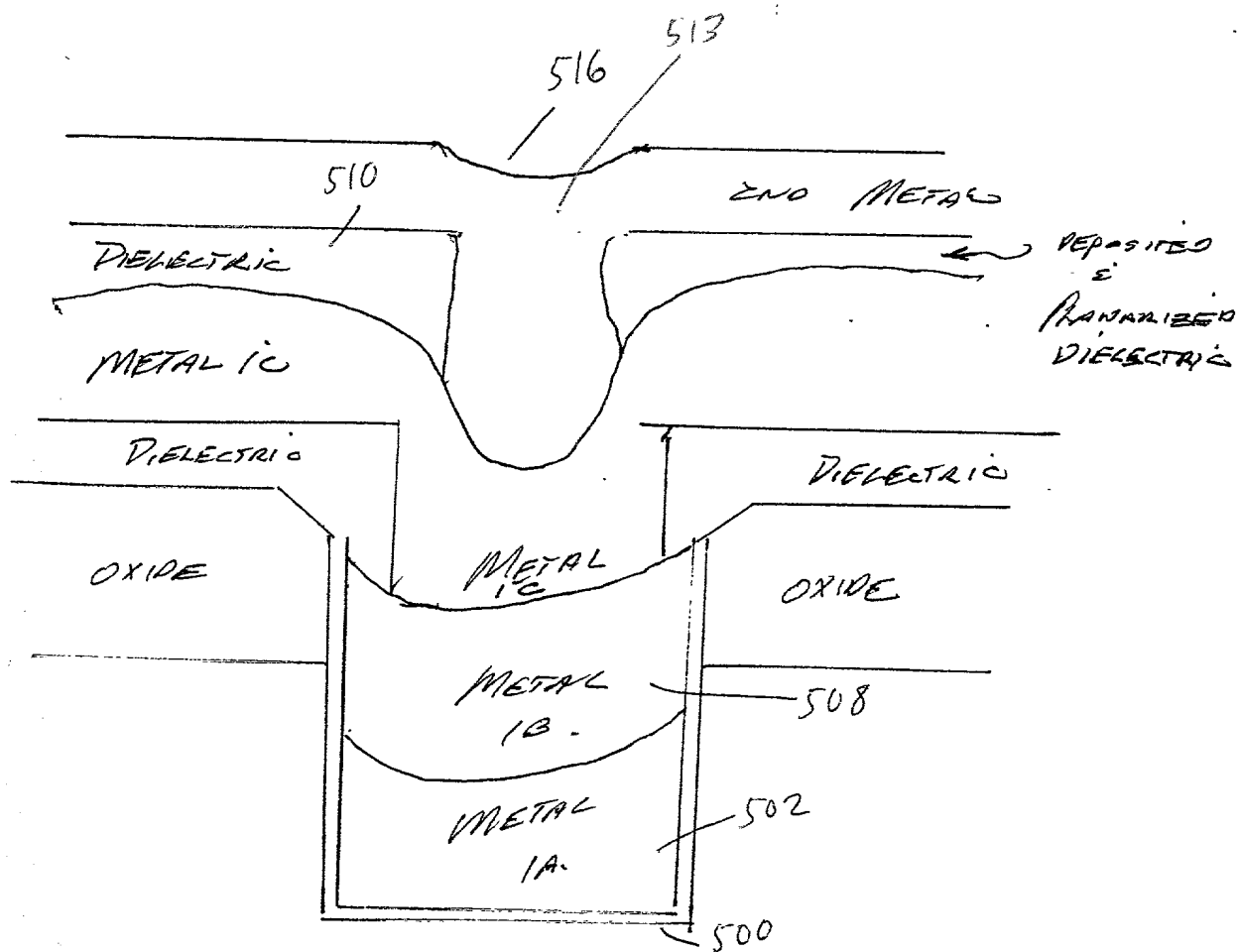
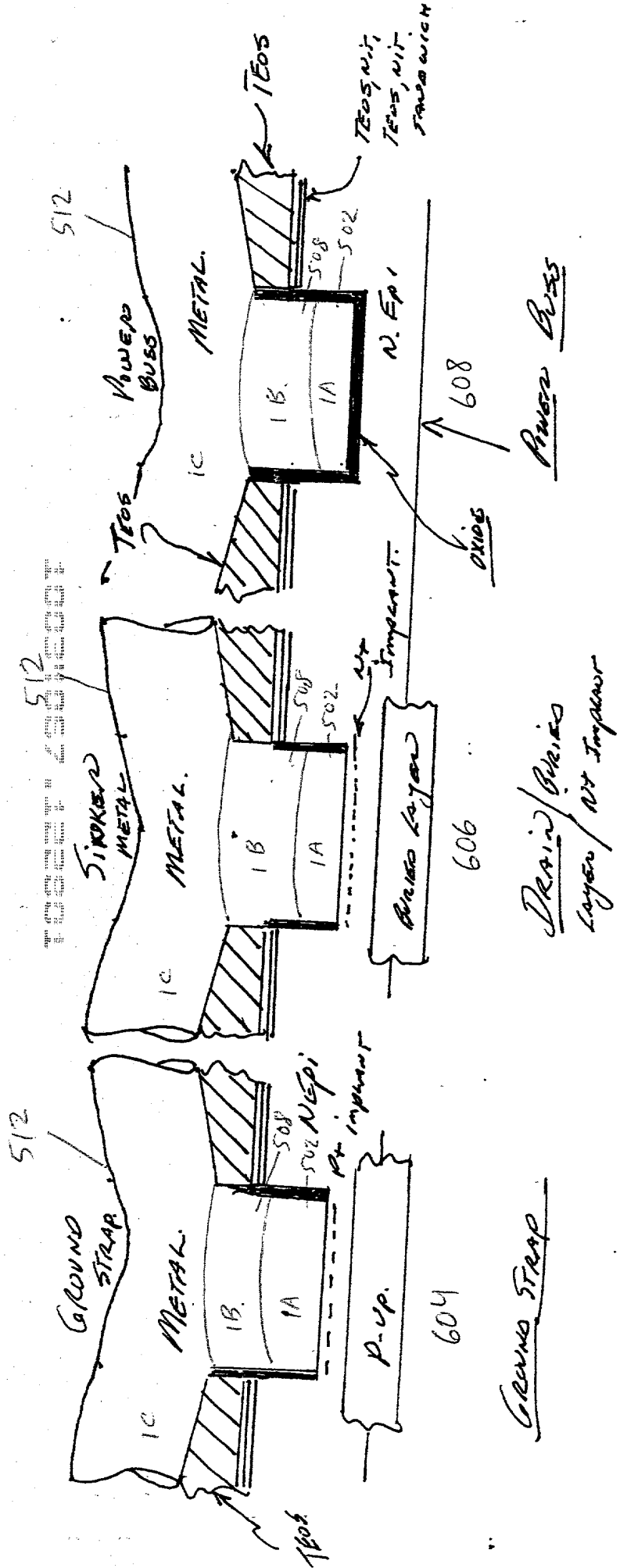


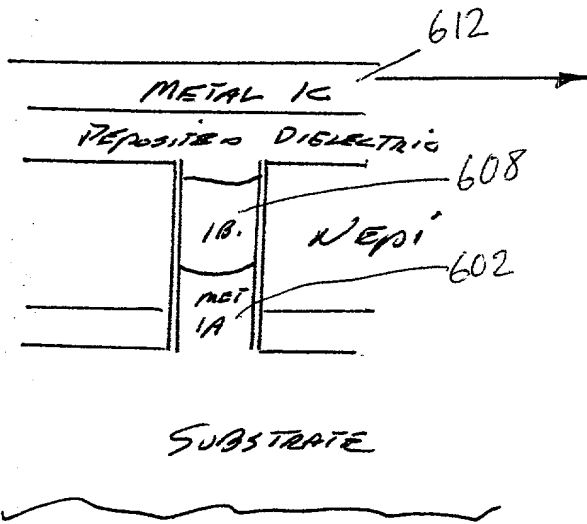
Fig. 10



GROUND STRAP / Power Buss / Drain Metal Sinkers

THIN OXIDE LAYER OF DIOSIDE  
 FOLLOWED BY 900Å TEOS - POLISH -  
 SLOTT MASK - METAL  
 METAL 1.5" - 2.0 mm deposited

Fig. 11 Power Metal.



**METAL 1C**  
 CONNECTS AN ISOLATED  
 ISLAND TO ADJACENT  
 ISOLATED EPI ISLANDS  
 AND CROSSES OVER THE  
 ISOLATION GROUND  
 STRAP BY NOT OPENING  
 A VIA IN THIS PORTION  
 TO ALLOW 1C TO BE  
 ISOLATED FROM GROUND.

Fig. 12